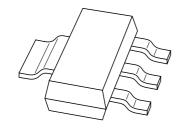
DISCRETE SEMICONDUCTORS

DATA SHEET



BSP50; BSP51; BSP52 NPN Darlington transistors

Product data sheet Supersedes data of 1997 Apr 22 1999 Apr 23



NPN Darlington transistors

BSP50; BSP51; BSP52

FEATURES

- High current (max. 1 A)
- Low voltage (max. 80 V)
- Integrated diode and resistor.

APPLICATIONS

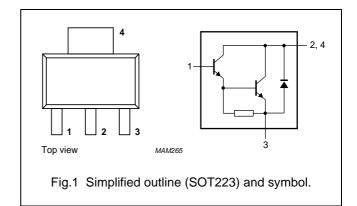
• Industrial high gain amplification.

DESCRIPTION

NPN Darlington transistor in a SOT223 plastic package. PNP complements: BSP60, BSP61 and BSP62.

PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | base |
| 2,4 | collector |
| 3 | emitter |



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

| SYMBOL | PARAMETER | CONDITIONS | | MAX. | UNIT |
|------------------|-------------------------------|----------------------------------|-----|------|------|
| V _{CBO} | collector-base voltage | open emitter | | | |
| | BSP50 | | _ | 60 | V |
| | BSP51 | | _ | 80 | V |
| | BSP52 | | _ | 90 | V |
| V _{CES} | collector-emitter voltage | V _{BE} = 0 | | | |
| | BSP50 | | _ | 45 | V |
| | BSP51 | | _ | 60 | V |
| | BSP52 | | _ | 80 | V |
| V _{EBO} | emitter-base voltage | open collector | _ | 5 | V |
| I _C | collector current (DC) | | _ | 1 | Α |
| I _{CM} | peak collector current | | _ | 2 | Α |
| I _B | base current (DC) | | _ | 100 | mA |
| P _{tot} | total power dissipation | T _{amb} ≤ 25 °C; note 1 | _ | 1.25 | W |
| T _{stg} | storage temperature | | -65 | +150 | °C |
| Tj | junction temperature | | _ | 150 | °C |
| T _{amb} | operating ambient temperature | | -65 | +150 | °C |

Note

1. Device mounted on a printed-circuit board, single sided copper, tinplated, mounting pad for collector 1 cm². For other mounting conditions, see *"Thermal considerations for the SOT223 in the General Part of associated Handbook"*.

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THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|---------------------|--|------------|-------|------|
| R _{th j-a} | thermal resistance from junction to ambient | note 1 | 96 | K/W |
| R _{th j-s} | thermal resistance from junction to solder point | | 17 | K/W |

Note

1. Device mounted on a printed-circuit board, single sided copper, tinplated, mounting pad for collector 1 cm². For other mounting conditions, see "Thermal considerations for the SOT223 in the General Part of associated Handbook".

CHARACTERISTICS

 $T_i = 25$ °C unless otherwise specified.

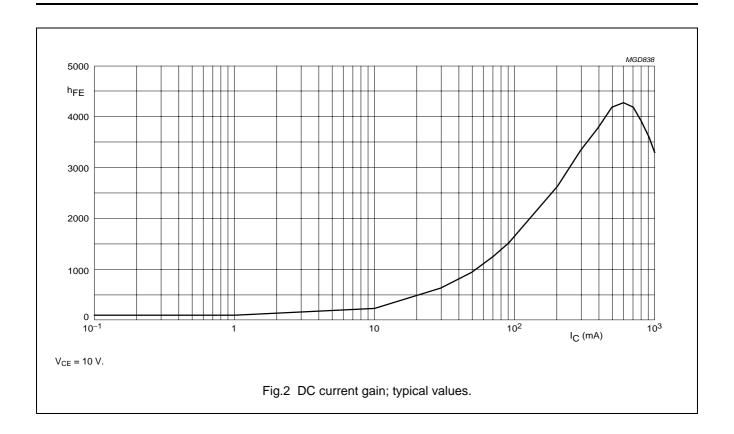
| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|---|---------------------------------|---|------|------|------|------|
| I _{CES} | collector cut-off current | | | | | |
| | BSP50 | $V_{BE} = 0; V_{CE} = 45 \text{ V}$ | _ | _ | 50 | nA |
| | BSP51 | $V_{BE} = 0; V_{CE} = 60 \text{ V}$ | _ | _ | 50 | nA |
| | BSP52 | V _{BE} = 0; V _{CE} = 80 V | _ | _ | 50 | nA |
| I _{EBO} | emitter cut-off current | I _C = 0; V _{EB} = 4 V | _ | _ | 50 | nA |
| h _{FE} | DC current gain | V _{CE} = 10 V; note 1; see Fig.2 | | | | |
| | | I _C = 150 mA | 1000 | _ | _ | |
| | | I _C = 500 mA | 2000 | _ | _ | |
| V _{CEsat} | collector-emitter saturation | $I_C = 500 \text{ mA}; I_B = 0.5 \text{ mA}$ | _ | _ | 1.3 | V |
| voltage | | $I_C = 500 \text{ mA}; I_B = 0.5 \text{ mA};$ $T_j = 150 \text{ °C}$ | _ | _ | 1.3 | V |
| V _{BEsat} | base-emitter saturation voltage | I _C = 500 mA; I _B = 0.5 mA | _ | _ | 1.9 | V |
| f _T | transition frequency | $I_C = 500 \text{ mA}; V_{CE} = 5 \text{ V}; f = 100 \text{ MHz}$ | _ | 200 | - | MHz |
| Switching times (between 10% and 90% levels); see Fig.3 | | | | | | |
| t _{on} | turn-on time | I _{Con} = 500 mA; I _{Bon} = 0.5 mA; | _ | 500 | _ | ns |
| t _{off} | turn-off time | $I_{Boff} = -0.5 \text{ mA}$ | _ | 1300 | - | ns |

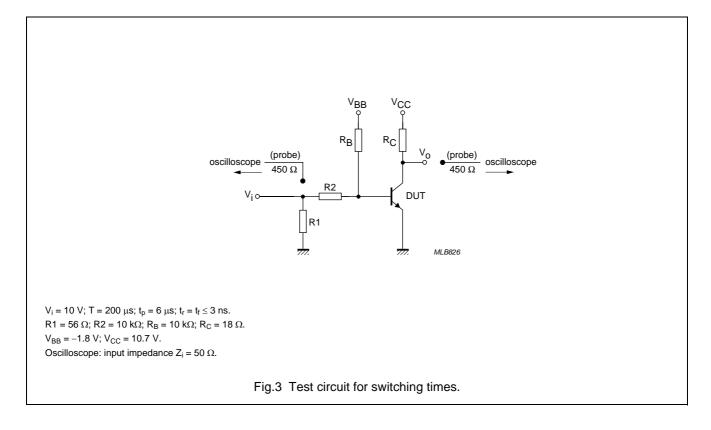
Note

1. Pulse test: $t_p \leq 300~\mu s;~\delta \leq 0.02.$

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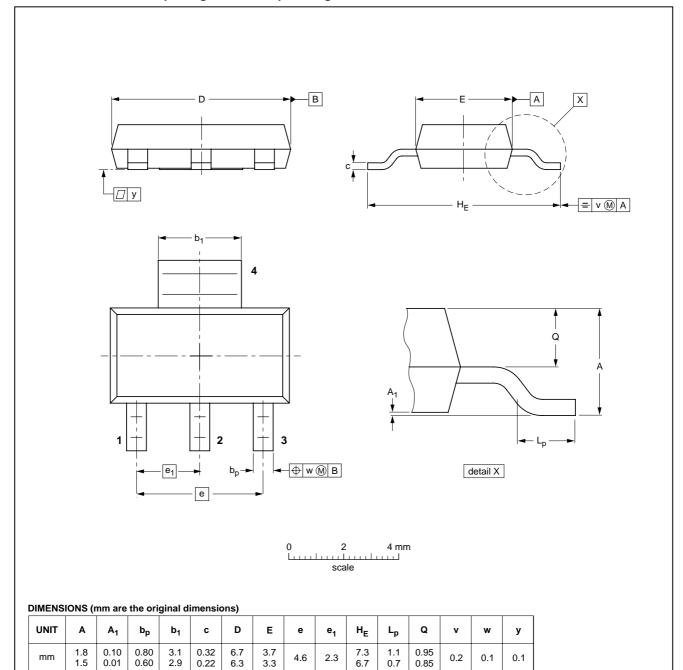
NPN Darlington transistors

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PACKAGE OUTLINE

Plastic surface mounted package; collector pad for good heat transfer; 4 leads

SOT223



| OUTLINE | REFERENCES | | | EUROPEAN | ICCUE DATE | |
|---------|------------|-------|-------|----------|------------|---------------------------------|
| VERSION | IEC | JEDEC | EIAJ | | PROJECTION | ISSUE DATE |
| SOT223 | | | SC-73 | | | 97-02-28 99-09-13 |

NPN Darlington transistors

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DATA SHEET STATUS

| DOCUMENT STATUS ⁽¹⁾ | PRODUCT STATUS ⁽²⁾ | DEFINITION |
|-----------------------------------|----------------------------------|---|
| Objective data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary data sheet | Qualification | This document contains data from the preliminary specification. |
| Product data sheet | Production | This document contains the product specification. |

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